

DUAL LAYER BARRIER FILM TECHNIQUES TO PREVENT RESIST POISONING

ABSTRACT OF THE DISCLOSURE

Provided is a process for forming a barrier film to prevent resist poisoning in a semiconductor device by depositing a second nitrogen-free barrier layer on top of a first barrier layer containing nitrogen. A low-k dielectric layer is formed over the second barrier layer. This technique maintains the low electrical leakage characteristics of the first barrier layer and reduces nitrogen poisoning of a photoresist layer subsequently applied.

10